

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK170V65Z

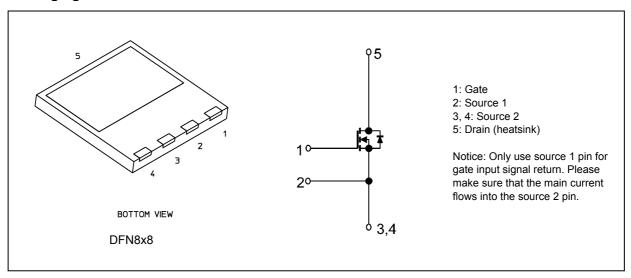
1. Applications

· Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.142 \Omega$ (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode: $V_{th} = 3$ to $4 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 0.73 \text{ mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	18	Α
Drain current (pulsed)	(Note 1)	I _{DP}	72	
Power dissipation (T _c	; = 25 °C)	P _D	150	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	225	mJ
Single-pulse avalanche current		I _{AS}	4.5	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	18	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	72	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

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Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.833	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 19.7 mH, I_{AS} = 4.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	_	2	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.73 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 9 A	_	0.142	0.17	Ω

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	1635	_	pF
Reverse transfer capacitance	C _{rss}		_	1.6	_	
Output capacitance	C _{oss}		_	40	_	
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	62	_	pF
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	_	3	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	16	_	ns
Switching time (turn-on time)	t _{on}		_	37	_	
Switching time (fall time)	t _f		_	4	_	
Switching time (turn-off time)	t _{off}		_	70	_	ns
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 9 A$	70	_		V/ns

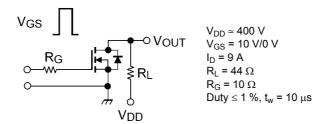


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$		29	1	nC
Gate-source charge 1	Q _{gs1}		_	9.5		
Gate-drain charge	Q_{gd}		_	8	_	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 18 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		V _{DD} = 400 V,	_	290	_	ns
Reverse recovery charge	Q _{rr}	$I_{DR} = 9 \text{ A, } V_{GS} = 0 \text{ V}$ -dI _{DR} /dt = 100 A/ μ s	_	3.3	_	μС
Peak reverse recovery current	I _{rr}	αι _{DR} /αι – 100 Ανμο	_	23	_	Α
Diode dv/dt ruggedness	dv/dt	$V_{DD} \le 400 \text{ V}, I_{DR} \le 9 \text{ A}, V_{GS} = 0 \text{ V}$	40	_	_	V/ns



7. Marking

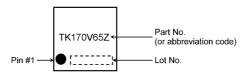


Fig. 7.1 Marking



8. Characteristics Curves (Note)

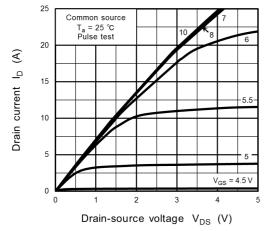


Fig. 8.1 I_D - V_{DS}

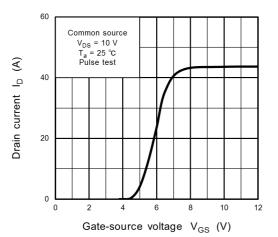
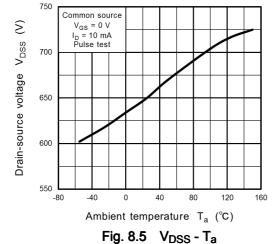


Fig. 8.3 I_D - V_{GS}



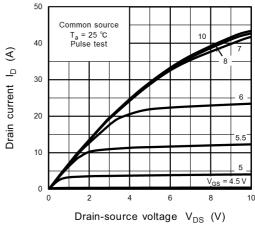


Fig. 8.2 I_D - V_{DS}

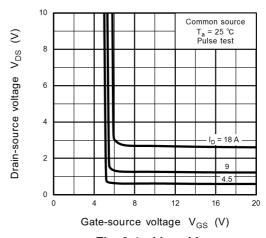


Fig. 8.4 V_{DS} - V_{GS}

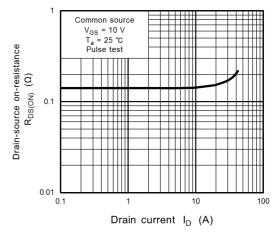
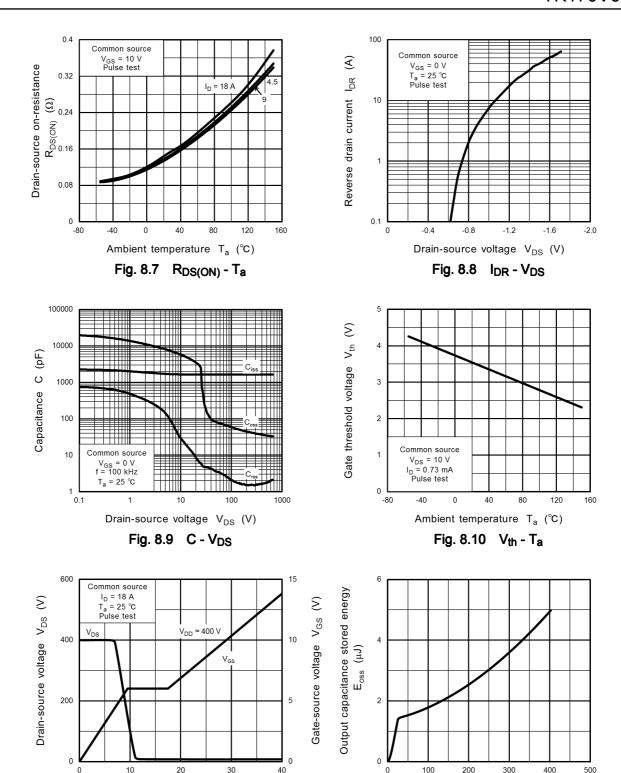


Fig. 8.6 R_{DS(ON)} - I_D

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Drain-source voltage V_{DS} (V) Fig. 8.12 E_{OSS} - V_{DS}



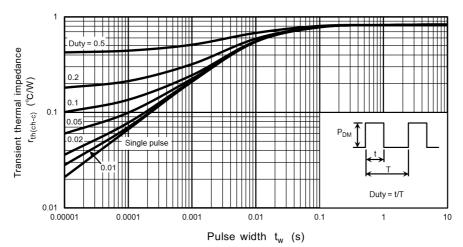


Fig. 8.13 rth - tw (Guaranteed Maximum)

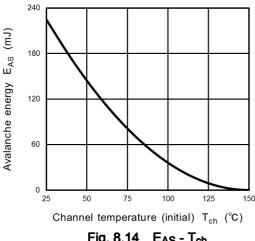


Fig. 8.14 EAS - Tch (Guaranteed Maximum)

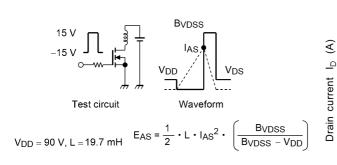


Fig. 8.16 Test Circuit/Waveform

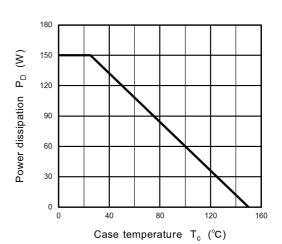


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

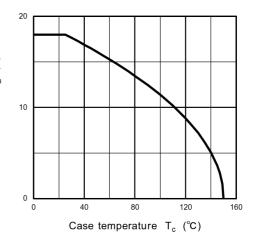


Fig. 8.17 I_D - T_c (Guaranteed Maximum)



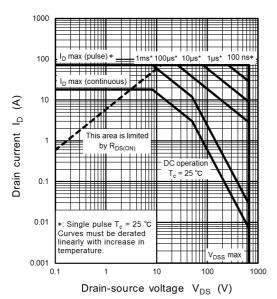


Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

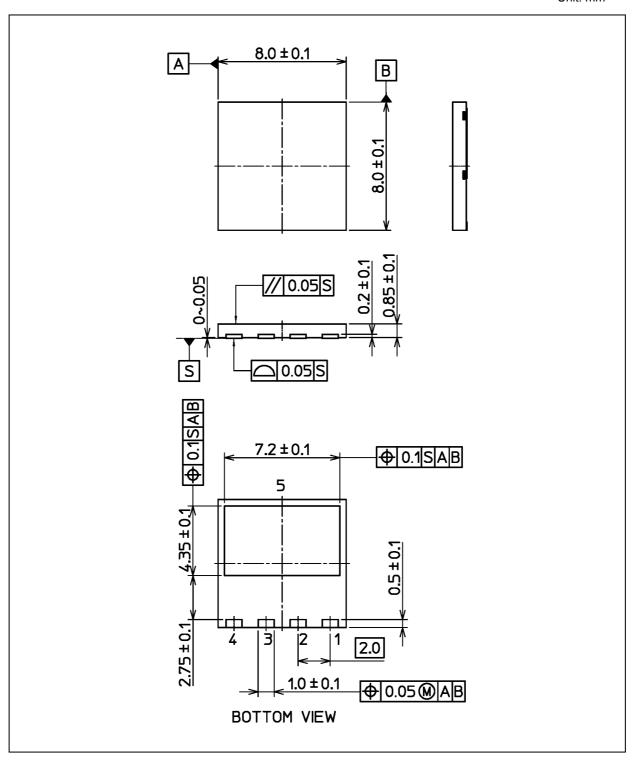
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.1.0



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	



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